

**SPECIFICATION AMENDMENTS:**

Please amend the specification as follows:

Please substitute the following annotated paragraph for paragraph number [0026]:

FIG. 4 is a cross-sectional view of a high frequency substrate in accordance with the third preferred embodiment of the invention. Referring to FIG. 4, the high frequency substrate 400 has two metal layers 402 and 406, a high-frequency signal transmission line 410, a low-frequency signal transmission line 418 and four dielectric layers 412, 414, 416 and 420. The dielectric layer 412 is on the metal layer 402 and the dielectric layer 412 is made of a high dielectric coefficient material; the value of the dielectric coefficient thereof is more than 4. The metal layer 406 is formed on the dielectric layer 412 and the dielectric layer ~~416~~ 420 is formed on the metal layer 406. The dielectric layer ~~416~~ 420 is possessed of openings 422 and 424, so that portions of the metal layer 406 are exposed via the openings 422 and 424. Further, the dielectric layers 414 and 416 are respectively filled within the opening 422 and within the opening 424 but are both on the metal layer 406, so that the dielectric layers 414, 416 and 420 are all on the metal layer 406. The dielectric layer 414 is made of a low dielectric coefficient material; the value of the dielectric coefficient thereof is less than 4. The dielectric layers 412 and 416 are both made of same high dielectric coefficient materials. The high-frequency signal transmission line 410 is on the dielectric layer 414 and a low-frequency signal transmission line 418 is on the dielectric layer 416.

Please replace the section of ABSTRACT with the following annotated of ABSTRACT:

A high frequency substrate includes a first metal layer, a first dielectric layer, a second metal layer, a second dielectric layer and a high-frequency signal transmission line. The first dielectric layer is formed on the first metal layer, and the second metal layer is formed on the first dielectric layer. The first and second metal layers are maintained in a stable voltage status due to the high dielectric coefficient of the first dielectric layer. Besides, the second dielectric layer is formed on the second metal layer. High speed and high frequency transmission are achieved when signals transmitting in the high-frequency transmission line formed on the second dielectric layer due to the low dielectric coefficient of the second dielectric layer.